

- AVAILABLE IN JAN, JANTX AND JANTXV  
PER MIL-PRF-19500/118
- GENERAL PURPOSE SILICON DIODES
- METALLURGICALLY BONDED

1N5194UR  
1N5195UR  
1N5196UR  
CDLL5194  
CDLL5195  
CDLL5196

## MAXIMUM RATINGS

Operating Temperature: -65°C to +175°C  
Storage Temperature: -65°C to +175°C  
Operating Current: 200 mA  
Derating: 1.2mA/°C from 25°C to 150°C  
1.0mA/°C from 150°C to 175°C  
Forward Current: 650mA

## ELECTRICAL CHARACTERISTICS @ 25°C, unless otherwise specified

TYPE	V <sub>RM</sub>	V <sub>RWM</sub>	I <sub>O</sub>	I <sub>O</sub> T <sub>A</sub> = +150°C	I <sub>FSM</sub> T <sub>P</sub> = 1/120 S T <sub>A</sub> = 25°C
	V <sub>(pk)</sub>	V <sub>(pk)</sub>	mA	mA	A
CDLL, 1N5194UR	80	70	200	50	2
CDLL, 1N5195UR	180	180	200	50	2
CDLL, 1N5196UR	250	225	200	50	2

TYPE	V <sub>F</sub> @100mA	I <sub>R1</sub> at V <sub>RWM</sub>	I <sub>R2</sub> at V <sub>RM</sub> T <sub>A</sub> = 25°C	I <sub>R3</sub> at V <sub>RWM</sub> T <sub>A</sub> = 150°C
	V dc	nA dc	μA	μA dc
CDLL, 1N5194UR	0.8 - 1.0	25	100	5
CDLL, 1N5195UR	0.8 - 1.0	25	100	5
CDLL, 1N5196UR	0.8 - 1.0	25	100	5

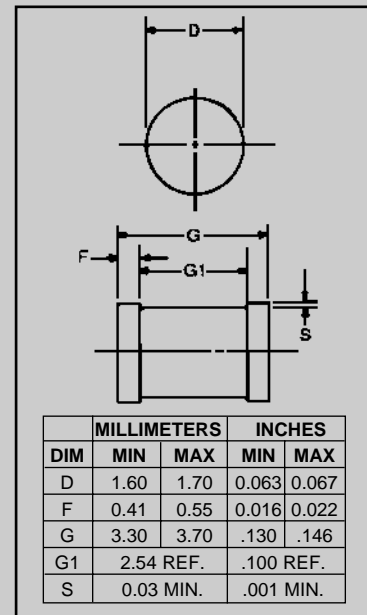


FIGURE 1

## DESIGN DATA

**CASE:** DO-213AA, Hermetically sealed glass case. (MELF, SOD-80, LL34)

**LEAD FINISH:** Tin / Lead

**THERMAL RESISTANCE:** (R<sub>QJEC</sub>):  
100 °C/W maximum

**THERMAL IMPEDANCE:** (Z<sub>QJX</sub>): 70  
°C/W maximum

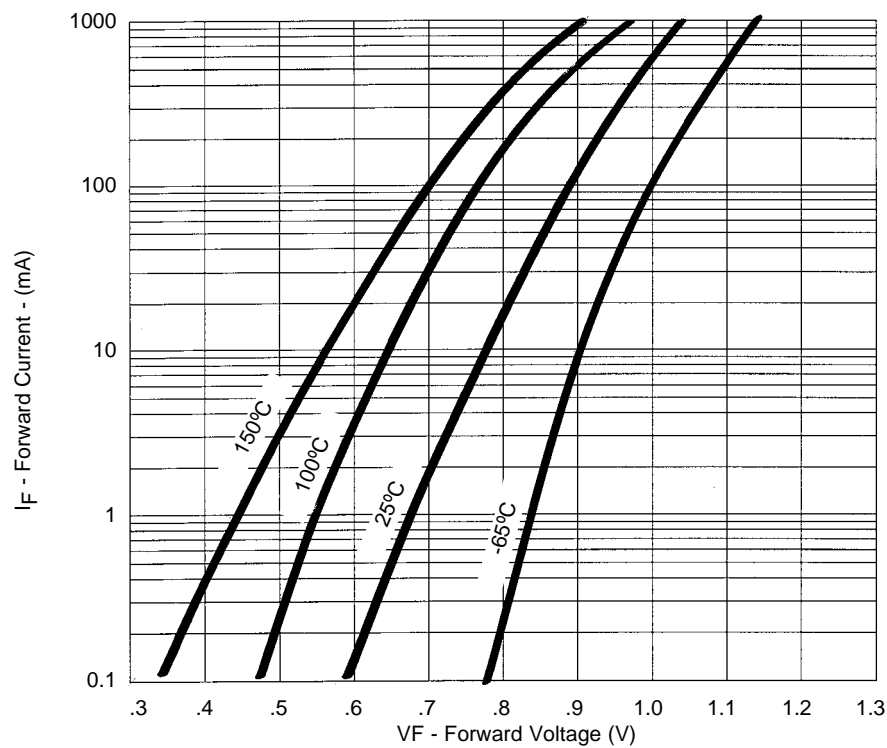
**POLARITY:** Cathode end is banded.

**MOUNTING POSITION:** Any.

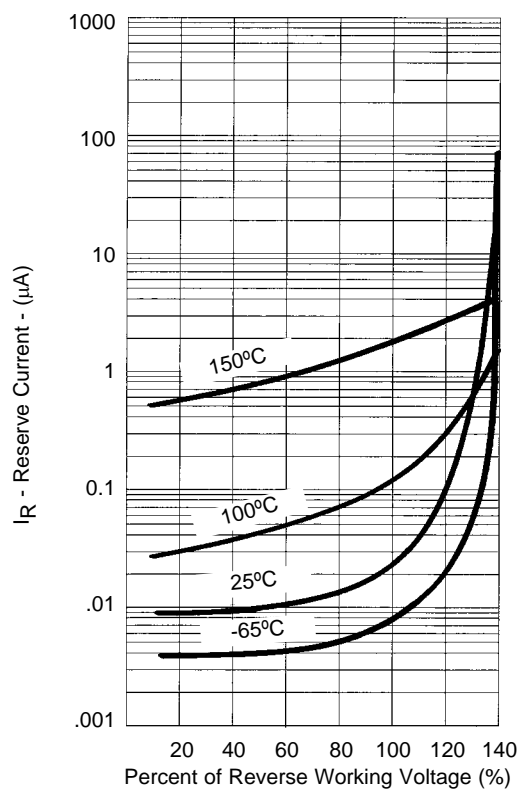
**MOUNTING SURFACE SELECTION:**  
The Axial Coefficient of Expansion (COE) Of this Device is Approximately +6PPM/°C. The COE of the Mounting Surface System Should Be Selected To Provide A Suitable Match With This Device.



# IN5194UR thru IN5196UR, CDLL5194 thru CDLL5196



**FIGURE 2**  
Typical Forward Current  
vs Forward Voltage



**NOTE :** All temperatures shown on graphs are junction temperatures

**FIGURE 3**  
Typical Reverse Current  
vs Reverse Voltage